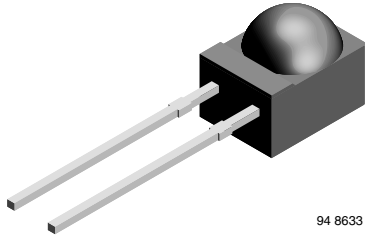


## Silicon PIN Photodiode, RoHS Compliant



94 8633

### DESCRIPTION

BPV22F is a PIN photodiode with high speed and high radiant sensitivity in a black, plastic package with side view lens and daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters. The lens achieves 80 % of sensitivity improvement in comparison with flat package.

### FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (in mm): 4.5 x 5 x 6
- Radiant sensitive area (in mm<sup>2</sup>): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- Fast response times
- Angle of half sensitivity:  $\phi = \pm 60^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


**RoHS**  
COMPLIANT

### APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSALxxxx series IR emitters

### PRODUCT SUMMARY

COMPONENT	$I_{ra}$ ( $\mu A$ )	$\phi$ (deg)	$\lambda_{0.5}$ (nm)
BPV22F	80	$\pm 60$	870 to 1050

#### Note

Test condition see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPV22F	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	60	V
Power dissipation	$T_{amb} \leq 25^\circ C$	$P_V$	215	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 100	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm <sup>2</sup>	$R_{thJA}$	350	K/W

#### Note

$T_{amb} = 25^\circ C$ , unless otherwise specified

<b>BASIC CHARACTERISTICS</b>						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50 \text{ mA}$	$V_F$		1	1.3	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}, E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10 \text{ V}, E = 0$	$I_{ro}$		2	30	nA
Diode capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	$C_D$		70		pF
Serial resistance	$V_R = 12 \text{ V}, f = 1 \text{ MHz}$	$R_S$		400		$\Omega$
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$V_o$		370		mV
Temperature coefficient of $V_o$	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$TK_{V_o}$		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	$I_k$		75		$\mu\text{A}$
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 \text{ V}$	$I_{ra}$	55	80		$\mu\text{A}$
Temperature coefficient of $I_{ra}$	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 10 \text{ V}$	$TK_{I_{ra}}$		0.1		%/K
Absolute spectral sensitivity	$V_R = 5 \text{ V}, \lambda = 870 \text{ nm}$	$s(\lambda)$		0.35		A/W
	$V_R = 5 \text{ V}, \lambda = 950 \text{ nm}$	$s(\lambda)$		0.6		A/W
Angle of half sensitivity		$\varphi$		$\pm 60$		deg
Wavelength of peak sensitivity		$\lambda_p$		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$		870 to 1050		nm
Quantum efficiency	$\lambda = 950 \text{ nm}$	$\eta$		90		%
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		$4 \times 10^{-14}$		W/ $\sqrt{\text{Hz}}$
Detectivity	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	$D^*$		$6 \times 10^{12}$		$\text{cm}\sqrt{\text{Hz/W}}$
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	$t_r$		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	$t_f$		100		ns
Cut-off frequency	$V_R = 12 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 870 \text{ nm}$	$f_c$		4		MHz
	$V_R = 12 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 950 \text{ nm}$	$f_c$		1		MHz

**Note**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

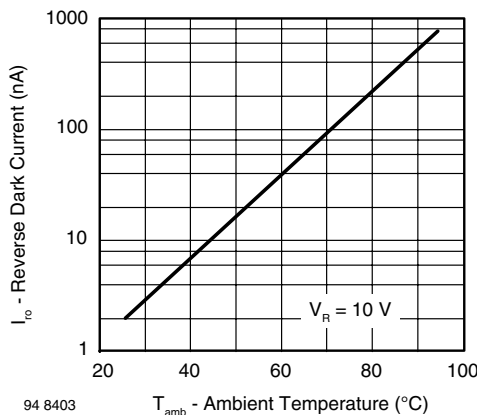


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

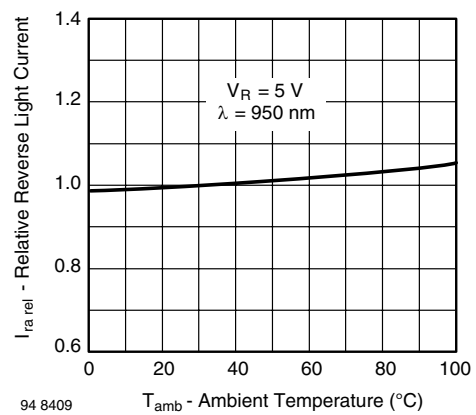
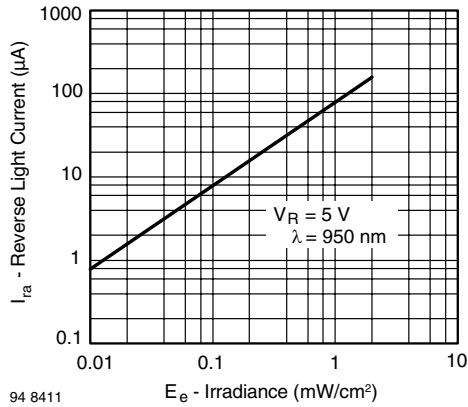
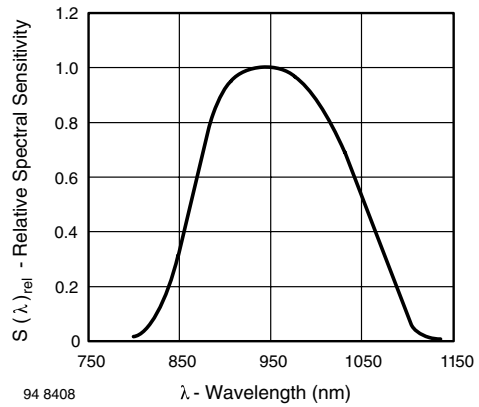


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



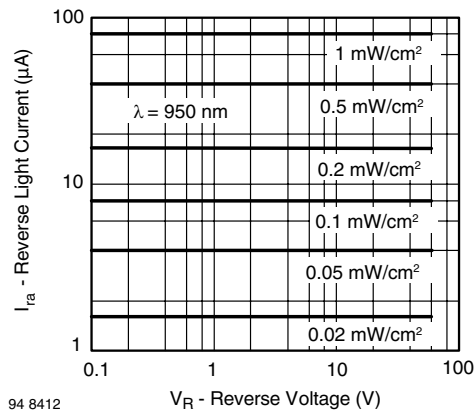
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Fig. 3 - Reverse Light Current vs. Irradiance



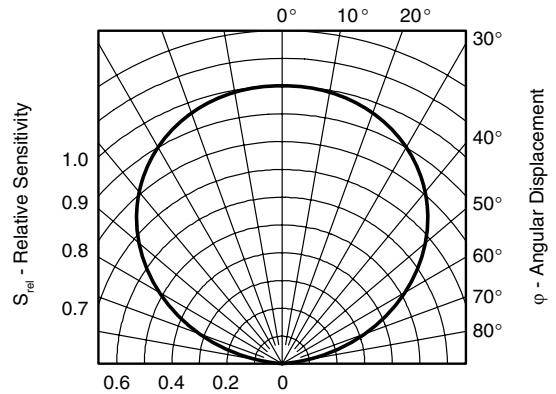
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Fig. 6 - Relative Spectral Sensitivity vs. Wavelength



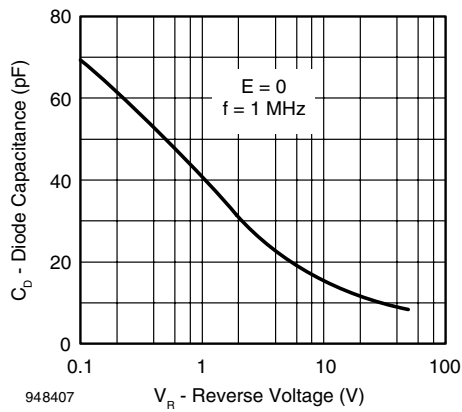
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Fig. 4 - Reverse Light Current vs. Reverse Voltage



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Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement



948407

Fig. 5 - Diode Capacitance vs. Reverse Voltage





## Disclaimer

All product specifications and data are subject to change without notice.

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